

# **isc Silicon NPN Power Transistor**

## **BD539A**

### **DESCRIPTION**

- DC Current Gain -
- :  $h_{FE} = 40(Min.)@I_{C} = 0.5A$
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min)
- Complement to Type BD540A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



### **APPLICATIONS**

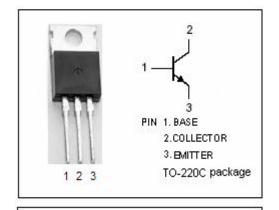
 Designed for use in medium power linear and switching applications.

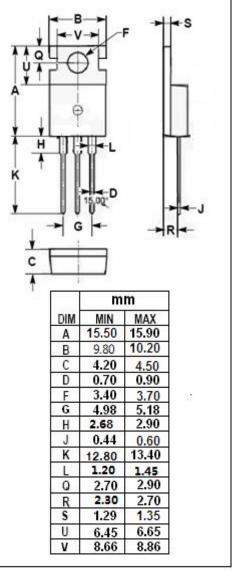
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	60	<b>V</b>	
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	5	Α	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	2	W	
	Collector Power Dissipation @ Tc=25°C	45		
TJ	Junction Temperature	150	$^{\circ}\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature Range	-65~150	°C	

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth j-c	Thermal Resistance, Junction to Case	2.78	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient		°C/W







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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; I <sub>B</sub> = 0	60		V
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 1A; I <sub>B</sub> = 0.125A		0.25	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.375A		0.8	V
V <sub>CE(sat)-3</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 1A		1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V		1.25	V
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 30V; I <sub>B</sub> = 0		0.3	mA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 60V; V <sub>BE</sub> = 0		0.2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0		1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 4V	40		
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	30		
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	12		

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